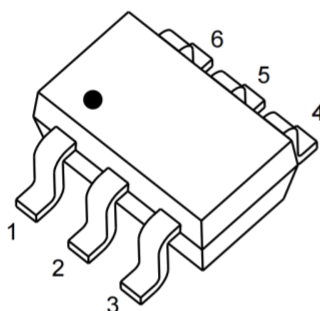


### Product Summary

- $V_{DS}$  30 V
- $I_{DS}$  800mA
- $R_{DS(ON)}$  (at  $V_{GS}=4.5V$ )  $\leq 450m\Omega$
- $R_{DS(ON)}$  (at  $V_{GS}=2.5V$ )  $\leq 650m\Omega$

### Package and Pin Configuration

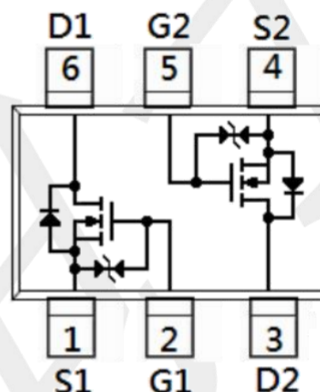


SOT-363

### Application

- Reverse Battery protection
- Load switch
- Power management
- Motor Control

### Circuit diagram



### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER                            | SYMBOL     | LIMIT       | UNIT |
|--------------------------------------|------------|-------------|------|
| Drain-Source Voltage                 | $V_{DS}$   | 30          | V    |
| Gate-Source Voltage                  | $V_{GS}$   | $\pm 12$    | V    |
| Continuous Drain Current             | $I_D$      | 800         | mA   |
| Drain Current-Pulsed (Note1)         | $I_{DM}$   | 2100        | mA   |
| Total Power Dissipation              | $P_{DTOT}$ | 0.35        | W    |
| Operating Junction Temperature Range | $T_J$      | -55 to +150 | °C   |
| Storage Temperature Range            | $T_{stg}$  | -55 to +150 | °C   |

### Thermal Characteristic

| PARAMETER                              |                      | Symbol     | Value | Unit |
|----------------------------------------|----------------------|------------|-------|------|
| Junction-to-Ambient Thermal Resistance | PCB Mount<br>(Note2) | $R_{thJA}$ | 833   | °C/W |

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. When mounted on 1" square PCB (FR4 material).

### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER                                               | CONDITIONS                                                                                   | SYMBOL              | MIN | TYP  | MAX | UNIT |
|---------------------------------------------------------|----------------------------------------------------------------------------------------------|---------------------|-----|------|-----|------|
| Static                                                  |                                                                                              |                     |     |      |     |      |
| Drain-Source Breakdown Voltage                          | V <sub>GS</sub> =0V, I <sub>D</sub> = 250μA                                                  | BV <sub>DSS</sub>   | 30  | --   | --  | V    |
| Gate-Source Threshold Voltage                           | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = 250μA                                    | V <sub>GS(th)</sub> | 0.5 | 0.8  | 1.2 | V    |
| Gate-Source Leakage                                     | V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V                                                  | I <sub>GSS</sub>    | --  | --   | ±20 | μA   |
| Zero Gate Voltage Drain Current                         | V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V                                                   | I <sub>DSS</sub>    | --  | --   | 1   | μA   |
|                                                         | V <sub>DS</sub> = 24V, T <sub>J</sub> =125°C                                                 |                     | --  | --   | 10  | μA   |
| Drain-Source On-State Resistance (Note 1)               | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.5A                                                | R <sub>DS(on)</sub> | --  | 350  | 450 | mΩ   |
|                                                         | V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 0.5A                                                |                     | --  | 450  | 650 |      |
| Forward Transconductance (Note 2)                       | V <sub>DS</sub> = 4V, I <sub>D</sub> = 0.3A                                                  | g <sub>fs</sub>     | --  | 1.1  | --  | S    |
| Dynamic (Note 2)                                        |                                                                                              |                     |     |      |     |      |
| Total Gate Charge (Note 3)                              | V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.25A, V <sub>GS</sub> = 4.5V                        | Q <sub>g</sub>      | --  | 2.6  | --  | nC   |
| Gate-Source Charge (Note 3)                             |                                                                                              | Q <sub>gs</sub>     | --  | 0.9  | --  |      |
| Gate-Drain Charge (Note 3)                              |                                                                                              | Q <sub>gd</sub>     | --  | 0.6  | --  |      |
| Input Capacitance                                       | V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, F= 1.0MHz                                       | C <sub>iss</sub>    | --  | 72.9 | --  | pF   |
| Output Capacitance                                      |                                                                                              | C <sub>oss</sub>    | --  | 18.3 | --  |      |
| Reverse Transfer Capacitance                            |                                                                                              | C <sub>rss</sub>    | --  | 7.4  | --  |      |
| Switching                                               |                                                                                              |                     |     |      |     |      |
| Turn-On Delay Time (Note 3)                             | V <sub>DD</sub> = 10V, I <sub>D</sub> = 0.5A, V <sub>GS</sub> = 4.5V, R <sub>GEN</sub> = 10Ω | t <sub>d(on)</sub>  | --  | 5.5  | --  | nS   |
| Rise Time (Note 3)                                      |                                                                                              | t <sub>r</sub>      | --  | 4.1  | --  |      |
| Turn-Off Delay Time (Note 3)                            |                                                                                              | t <sub>d(off)</sub> | --  | 14.5 | --  |      |
| Fall Time (Note 3)                                      |                                                                                              | t <sub>f</sub>      | --  | 6.5  | --  |      |
| Source-Drain Diode Ratings and Characteristics (Note 2) |                                                                                              |                     |     |      |     |      |
| Forward Voltage                                         | V <sub>GS</sub> = 0V, I <sub>F</sub> = 0.5A                                                  | V <sub>SD</sub>     | --  | 0.8  | 1.2 | V    |

Notes: 1. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

2. Guaranteed by design, not subject to production testing.

3. Independent of operating temperature

### TYPICAL CHARACTERISTICS

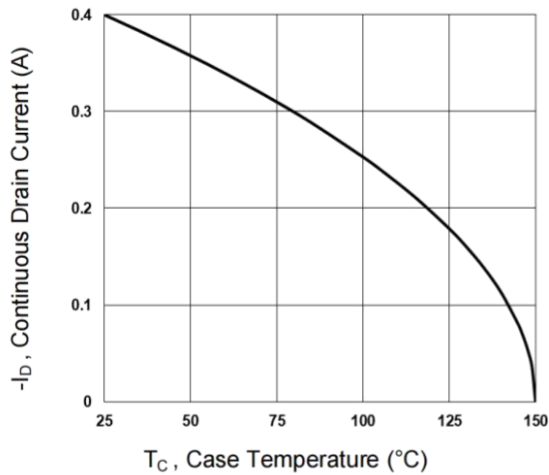


Figure 1. Continuous Drain Current vs.  $T_c$

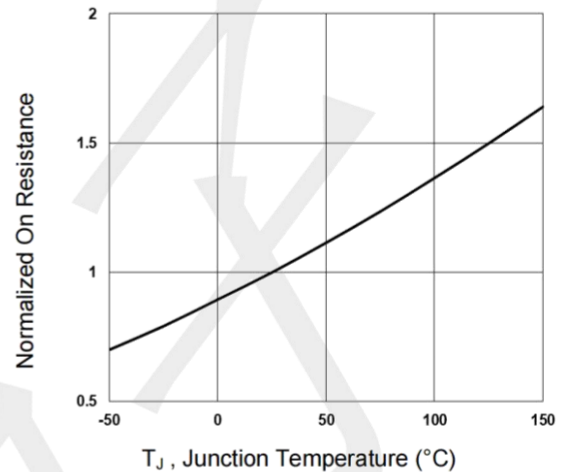


Figure 2. Normalized  $R_{DS(on)}$  vs.  $T_J$

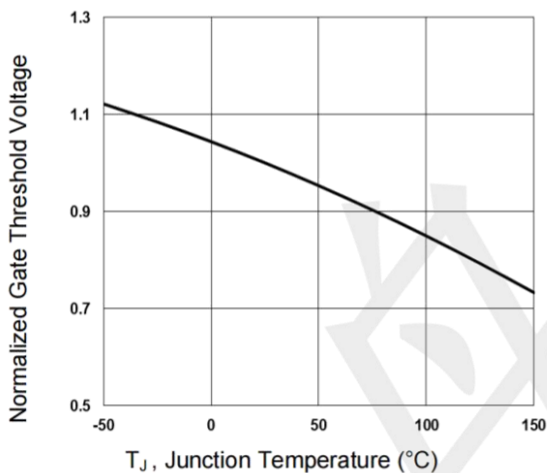


Figure 3. Normalized  $V_{th}$  vs.  $T_J$

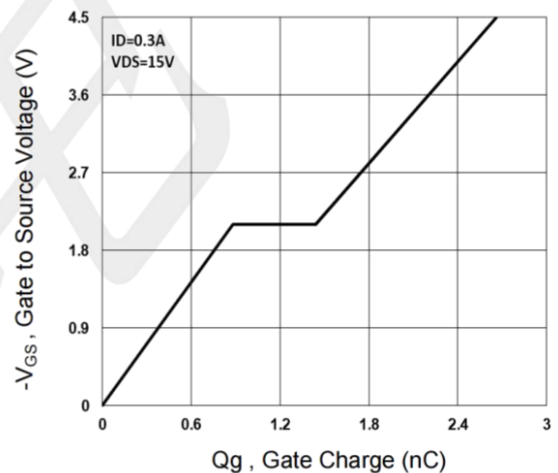


Figure 4. Gate Charge Waveform

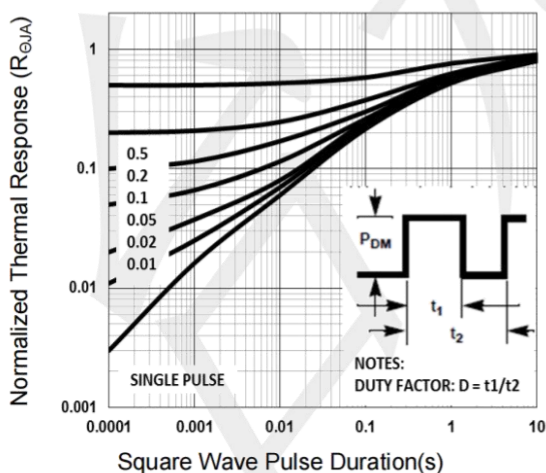


Figure 5. Normalized Transient Response

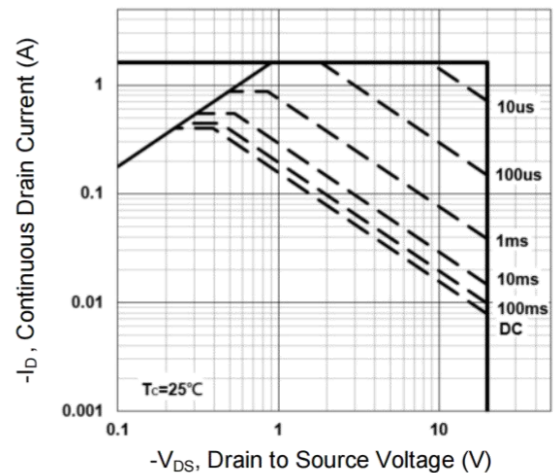
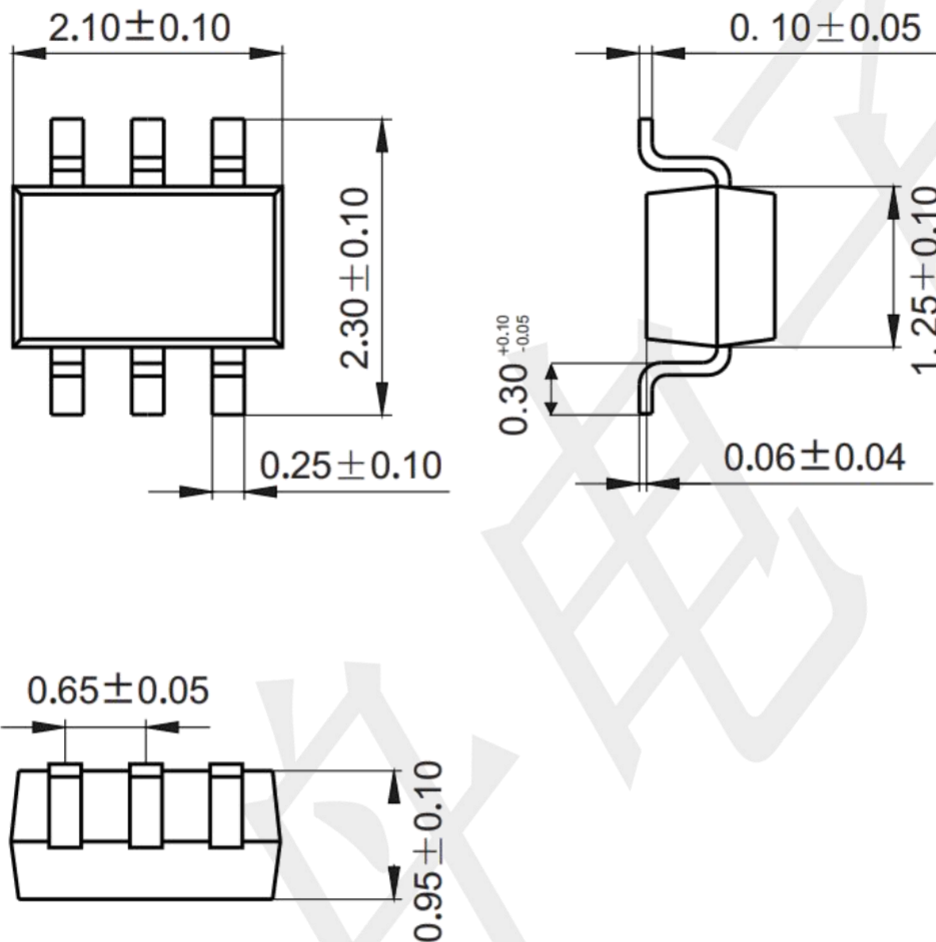


Figure 6. Maximum Safe Operation Area

**Package information (Unit: mm)**

SOT363



**Mounting Pad Layout (unit: mm)**

